

2SC3874

Silicon NPN triple diffusion planar type

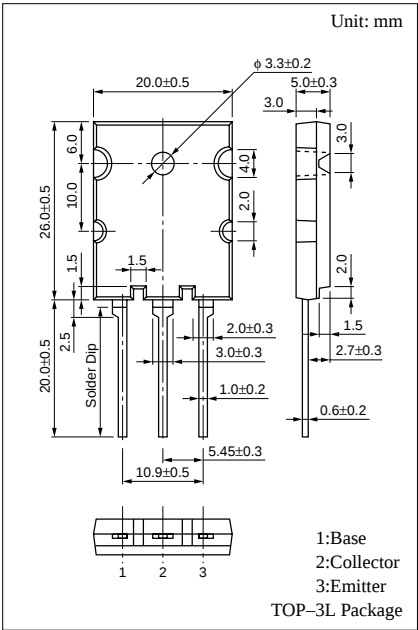
For high breakdown voltage high-speed switching

Features

- High-speed switching
- High collector to base voltage V_{CBO}
- Wide area of safe operation (ASO)
- Satisfactory linearity of forward current transfer ratio h_{FE}

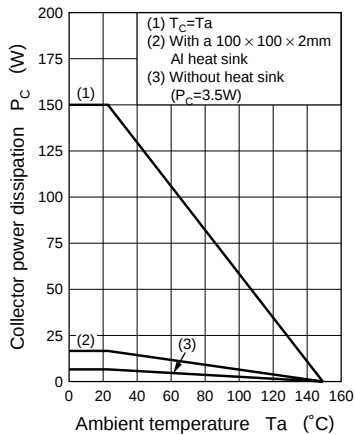
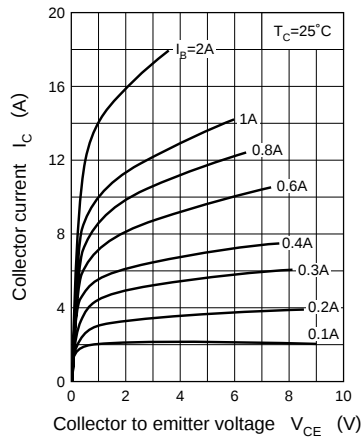
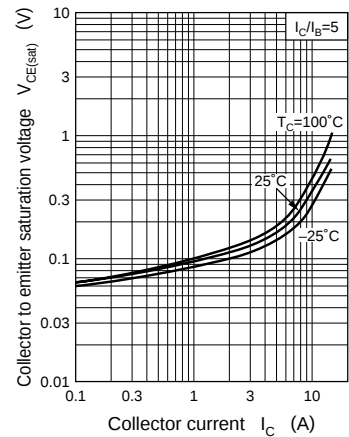
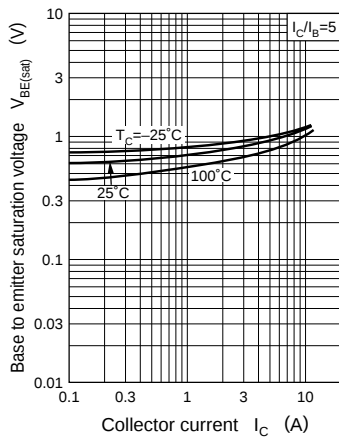
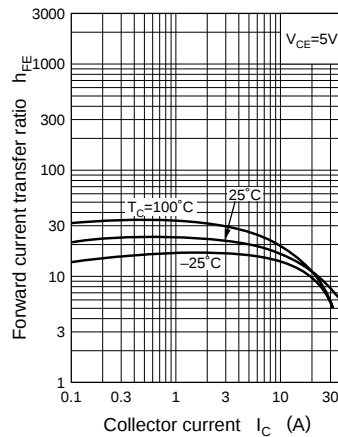
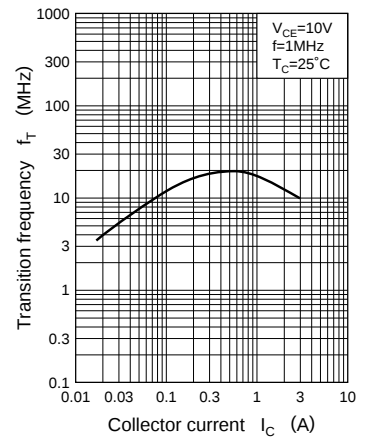
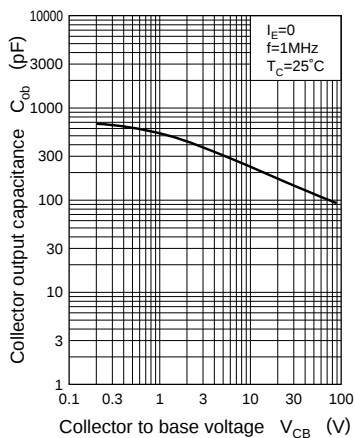
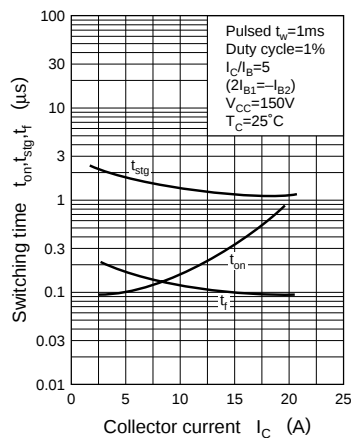
Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V_{CES}	500	V
	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	25	A
Collector current	I_C	15	A
Base current	I_B	5	A
Collector power dissipation	P_C	150	W
		3.5	
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}C$

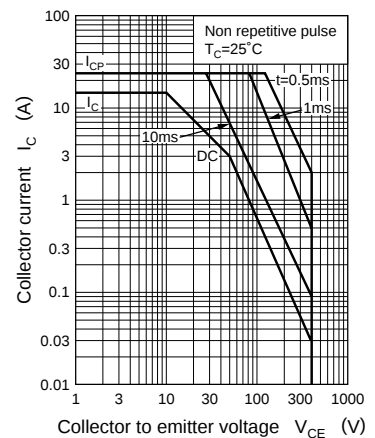


Electrical Characteristics ($T_C=25^{\circ}C$)

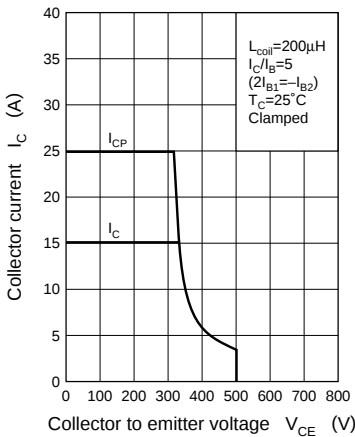
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 500V, I_E = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 5V, I_C = 0$			100	μA
Collector to emitter voltage	V_{CEO}	$I_C = 10mA, I_B = 0$	400			V
Forward current transfer ratio	h_{FE1}	$V_{CE} = 5V, I_C = 0.1A$	15			
	h_{FE2}	$V_{CE} = 5V, I_C = 10A$	8			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10A, I_B = 2A$			1.0	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10A, I_B = 2A$			1.5	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 1A, f = 1MHz$		20		MHz
Turn-on time	t_{on}	$I_C = 10A, I_{B1} = 2A, I_{B2} = -4A, V_{CC} = 150V$			0.7	μs
Storage time	t_{stg}				2.0	μs
Fall time	t_f				0.3	μs

$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_C$  $C_{ob} - V_{CB}$  $t_{on}, t_{stg}, t_f - I_C$ 

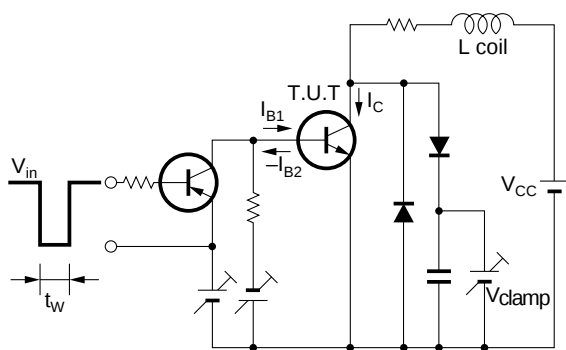
Area of safe operation (ASO)



Area of safe operation, reverse bias ASO



Reverse bias ASO measuring circuit



$R_{th}(t) - t$

